

AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

In the Claims

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Claim 1 (currently amended): A nitride-based semiconductor light-emitting device comprising:

- a silicon doped n-type GaN-based substrate; and
- a semiconductor stacked-layer structure including a plurality of nitride-based semiconductor layers grown on said GaN-based substrate by vapor phase deposition, said GaN-based substrate having an interface region contacting said semiconductor stacked-layer structure and said interface region containing oxygen atoms at concentration n in the range of $2 \times 10^{16} \leq n \leq 10^{22} \text{ cm}^{-3}$ and said GaN-based substrate containing chlorine.

Claim 2 (cancelled)

Claim 3 (original): The nitride-based semiconductor light-emitting device according to claim 1, wherein said GaN-based substrate contains oxygen.

Claim 4 (original): The nitride-based semiconductor light-emitting device according to claim 1, wherein

said plurality of nitride-based semiconductor layers included in said semiconductor stacked-layer structure include a layer contacting said GaN-based substrate, and said layer contacting said GaN-based substrate contains oxygen.

Claim 5 (currently amended): A nitride-based semiconductor light-emitting device comprising:

a GaN-based substrate including a p-type impurity; and
a semiconductor stacked-layer structure including a plurality of nitride-based semiconductor layers grown on said GaN-based substrate by vapor phase deposition,
said GaN-based substrate having an interface region contacting said semiconductor stacked-layer structure and said interface region containing oxygen atoms at concentration n in the range of $2 \times 10^{16} \leq n \leq 10^{22} \text{ cm}^{-3}$ and said GaN-based substrate containing chlorine.

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amp.* Claim 6 (previously added): The nitride-based semiconductor light-emitting device according to claim 5 wherein said p-type impurity includes magnesium.

Claim 7 (Cancelled)

Claim 8 (previously added): The nitride-based semiconductor light-emitting device according to claim 5 wherein said GaN-based substrate contains oxygen.

Claim 9 (previously added): The nitride-based semiconductor light-emitting device according to claim 5 wherein said plurality of nitride-based semiconductor layers included in said semiconductor stacked-layer structure include a layer contacting said GaN-based substrate, and said layer contacting said GaN-based substrate contains oxygen.
